Abstracts

Pulsed Power Performance of GaAs FETS at X-Band

S.J. Temple, Z. Galani, J. Dormail, R.M. Healy and B.S. Hewitt. "Pulsed Power Performance of GaAs FETS at X-Band." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 177-179.

The pulsed operation of X-band amplifiers using 4.8 mm power FETs resulted in a nominal output power improvement of 2 dB when operated at elevated drain voltages of up to 18 volts. An ouptut power of 6 W peak with 6 dB gain at 10 GHz was obtained from a balanced amplifier.

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